WHAT IS CLAIMED IS:

1. Storage water used for storage of a silicon wafer in water, wherein the storage water contains Cu at a concentration of 0.01 ppb or less.

2. Storage water used for storage of a silicon wafer in water according to Claim 1, wherein the storage water contains a surfactant.

3. A method of storing a silicon wafer in water, wherein the silicon wafer is stored in water or a chemical solution which does not cause degradation of oxide dielectric breakdown voltage due to copper contamination.

4. A method of storing a silicon wafer in water, wherein storage water containing Cu at a concentration of 0.01 ppb or less is used.

5. A method of storing a silicon wafer in water according to Claim 4, wherein storage water containing a surfactant is used.

6. A method of storing a silicon wafer in water according to Claim 4, wherein the silicon wafer to be stored has a hydrophobic surface.

7. A method of storing a silicon wafer in water

according to Claim 5, wherein the silicon wafer to be stored has a hydrophobic surface.

8. A method of storing a silicon wafer in water according to Claim 4, wherein the silicon wafer is stored immediately after polishing.

9. A method of storing a silicon wafer in water according to Claim 5, wherein the silicon wafer is stored immediately after polishing.

10. A method of storing a silicon wafer in water according to Claim 6, wherein the silicon wafer is stored immediately after polishing.

11. A method of storing a silicon wafer in water according to Claim 7, wherein the silicon wafer is stored immediately after polishing.

12. A method of storing a silicon wafer in a storage solution, wherein the storage solution is mainly formed of water or a chemical solution, to which a chelating agent is added.

13. A method of storing a silicon wafer in a storage solution according to Claim 12, wherein the silicon wafer to be stored has a hydrophobic surface.

14. A method of storing a silicon wafer in a storage solution according to Claim 12, wherein the chemical solution to which the chelating agent is added is an alkaline solution.

15. A method of storing a silicon wafer in a storage solution according to Claim 13, wherein the chemical solution to which the chelating agent is added is an alkaline solution.

16. A method of storing a silicon wafer in a storage solution according to Claim 12, wherein a surfactant is added to the water or chemical solution to which the chelating agent is added.

17. A method of storing a silicon wafer in a storage solution according to Claim 13, wherein a surfactant is added to the water or chemical solution to which the chelating agent is added.

18. A method of storing a silicon wafer in a storage solution according to Claim 14, wherein a surfactant is added to the water or chemical solution to which the chelating agent is added.

19. A method of storing a silicon wafer in a storage

solution according to Claim 12, wherein the chelating agent has a chelate compound production performance not lower than that of NTA.

20. A method of storing a silicon wafer in a storage solution according to Claim 12, wherein the chelating agent is selected from the group consisting of NTA, EDTA, DTPA, CyDTA, salts thereof, and a mixture thereof.

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